

Wenyuan Sun

List of Publications by Year in descending order

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Version: 2024-02-01

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papers

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1684188

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docs citations

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times ranked

338
citing authors

#	ARTICLE	IF	CITATIONS
1	Impact of Traps on the Adjacent Channel Power Ratios of GaN HEMTs. IEEE Electron Device Letters, 2020, 41, 816-819.	3.9	5
2	Breakdown Characteristics of $\text{Al}_{0.22}\text{Ga}_{0.78}\text{O}_3/\text{Ga}_2\text{O}_3/\text{Ga}_2\text{O}_3$ Field-Plated Modulation-Doped Field-Effect Transistors. IEEE Electron Device Letters, 2019, 40, 1241-1244.	3.9	82
3	Evaluation of Low-Temperature Saturation Velocity in $\text{Al}_x\text{Ga}_{1-x}\text{O}_3/\text{Ga}_2\text{O}_3$ Modulation-Doped Field-Effect Transistors. IEEE Transactions on Electron Devices, 2019, 66, 1574-1578.	3.0	66
4	Investigation of Trap-Induced Threshold Voltage Instability in GaN-on-Si MISHEMTs. IEEE Transactions on Electron Devices, 2019, 66, 890-895.	3.0	15
5	High Al-Content AlGaIn Transistor With 0.5 A/mm Current Density and Lateral Breakdown Field Exceeding 3.6 MV/cm. IEEE Electron Device Letters, 2018, 39, 256-259.	3.9	46